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APPLICATION NO.	F	ILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO
09/939,253		08/24/2001	James M. Derderian	4830US (01-0106)	2189
24247	7590	02/28/2003		•	
TRASK BI			EXAMINER		
P.O. BOX 2550 SALT LAKE CITY, UT 84110				WILLIAMS, ALEXANDER O	
				ART UNIT	PAPER NUMBER
				2826	14
				DATE MAILED: 02/28/2003	//

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)					
Office Action Comments	09/939,253	DERDERIAN, JAMES M.					
. Office Action Summary	Examiner	Art Unit					
	Alexander O Williams	2826					
The MAILING DATE of this communication app Period for Reply	pears on the cover sheet with the o	correspondence address					
A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.1 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a repl - If NO period for reply is specified above, the maximum statutory period of Failure to reply within the set or extended period for reply will, by statute - Any reply received by the Office later than three months after the mailing en.ned patent term adjustment. See 37 CFR 1.704(b). Status	36(a). In no event, however, may a reply be tir y within the statutory minimum of thirty (30) day will apply and will expire SIX (6) MONTHS from , cause the application to become ABANDONE	mely filed as will be considered timely. It the mailing date of this communication. ED (35 U.S.C. § 133).					
1) $oxed{\boxtimes}$ Responsive to communication(s) filed on $\underline{09}$ $\underline{1}$	December 2002						
2a) $igotimes$ This action is FINAL . 2b) $igodium$ Th	is action is non-final.						
3) Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under <i>Ex parte Quayle</i> , 1935 C.D. 11, 453 O.G. 213. Disposition of Claims							
4) Claim(s) 1-102 is/are pending in the application	on.						
4a) Of the above claim(s) 1-13,17-26,31-33,37-40 and 42-44 is/are withdrawn from consideration.							
5) Claim(s) is/are allowed.							
6) Claim(s) 1-13,17-26,31-33,37-40 and 42-44 is/	are rejected.						
7) Claim(s) is/are objected to.							
8) Claim(s) are subject to restriction and/o	r election requirement.						
() The specification is objected to by the Examine	r.						
10)⊠ The drawing(s) filed on <u>29 <i>March 2002</i> is/are: a)</u> accepted or b) objected to by the Examiner.							
Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).							
11) ☐ The proposed drawing correction filed on is: a) ☐ approved b) ☐ disapproved by the Examiner.							
If approved, corrected drawings are required in reply to this Office action.							
12) ☐ The oath or declaration is objected to by the Examiner.							
Priority under 35 U.S.C. §§ 119 and 120							
13) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).							
a) ☐ All b) ☐ Some * c) ☐ None of:							
1. Certified copies of the priority documents	s have been received.						
2. Certified copies of the priority documents	s have been received in Applicati	on No					
3. Copies of the certified copies of the prior application from the International But 5 See the attached detailed Office action for a list	reau (PCT Rule 17.2(a)).	-					
14) Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).							
a) ☐ The translation of the foreign language provisional application has been received. 15)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.							
Attachment(s)							
 Notice of References Cited (PTO-892) Notice of Draftsperson's Patent Drawing Review (PTO-948) Information Disclosure Statement(s) (PTO-1449) Paper No(s) 	5) 🔲 Notice of Informal F	v (PTO-413) Paper No(s) Patent Application (PTO-152)					

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Serial Number: 09/939253 Attorney's Docket #: 4830US(01-0106)

Filing Date: 8/24/01;

Applicant: Derderian

Examiner: Alexander Williams

Applicant's Amendment in Paper # 13, filed 12/9/02, has been acknowledged. The claims being examined are claims 1 to 13, 17-26, 31 to 33, 37 to 40 and 42 to 44

This application contains claims 14 to 16, 27 to 30, 34 to 36, 41 and 48 to 67 drawn to an invention non-elected without traverse in Paper No. 11.

This application contains claims 68 to 102 drawn to an invention non-elected with traverse in Paper No. 9.

The following is a quotation of the appropriate paragraphs of 35 U.S.C. § 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless --

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all

Claims 1 to 13, 17 to 26, 31 to 33, 37 to 40 and 42 to 44 are rejected under 35 U.S.C. § 102(e) as being anticipated by Mueller et al. (U.S. Patent # 6,316,786 B1).

For example, in claim 1, Mueller et al. (figures 1A to 4) specifically figure 1B show a semiconductor device 10 for use in a stacked multi-chip assembly 11,16, comprising: a semiconductor die 16; and a spacer layer 13,15,12,14 comprising dielectric material formed on at least a portion of a surface of said semiconductor die and protruding therefrom substantially a predetermined distance that said semiconductor die and an adjacent semiconductor die of said stacked multi-chip assembly are to be spaced apart from one another, said spacer layer including voids communicating with a lateral periphery thereof.

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For example, in claim 19, Mueller et al. (figures 1A to 4) specifically figure 1B show a semiconductor device assembly 10, comprising: a first semiconductor device 11; a nonconfluent spacer layer 12-14 comprising dielectric material and being positioned on a surface of said first semiconductor device, a second semiconductor device 16 positioned over said first semiconductor device, a surface of said second semiconductor device being adhered to said nonconfluent spacer layer.

Claims 1 to 13, 17 and 18 are rejected under 35 U.S.C. § 102(e) as being anticipated by Chang et al. (U.S. Patent # 2002/0070463 A1).

For example, in claim 1, Chang et al. (figures 1 to 10) specifically 1 show a semiconductor device for use in a stacked multi-chip assembly, comprising: a semiconductor die 30; and a spacer layer 32,36 comprising dielectric material formed on at least a portion of a surface of said semiconductor die and protruding therefrom substantially a predetermined distance that said semiconductor die and an adjacent semiconductor die of said stacked multi-chip assembly are to be spaced apart from one another, said spacer layer including voids communicating with a lateral periphery thereof.

Response

Applicant's arguments filed 12/9/02 have been fully considered, but are moot in view of the new grounds of rejections detailed above.

The insertion of Applicant's additional claimed language, for example, "in claims 1 and 19" cause for further search and consideration to make this action final.

Applicant's amendment necessitated the new grounds of rejection. Accordingly, **THIS ACTION IS MADE FINAL**. See M.P.E.P. § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 C.F.R. § 1.136(a).

A SHORTENED STATUTORY PERIOD FOR RESPONSE TO THIS FINAL
ACTION IS SET TO EXPIRE THREE MONTHS FROM THE DATE OF THIS ACTION.
IN THE EVENT A FIRST RESPONSE IS FILED WITHIN TWO MONTHS OF THE
MAILING DATE OF THIS FINAL ACTION AND THE ADVISORY ACTION IS NOT
MAILED UNTIL AFTER THE END OF THE THREE-MONTH SHORTENED

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STATUTORY PERIOD, THEN THE SHORTENED STATUTORY PERIOD WILL EXPIRE ON THE DATE THE ADVISORY ACTION IS MAILED, AND ANY EXTENSION FEE PURSUANT TO 37 C.F.R. § 1.136(a) WILL BE CALCULATED FROM THE MAILING DATE OF THE ADVISORY ACTION. IN NO EVENT WILL THE STATUTORY PERIOD FOR RESPONSE EXPIRE LATER THAN SIX MONTHS FROM THE DATE OF THIS FINAL ACTION.

The listed references are cited as of interest to this application, but not applied at this time.

Field of Search	Date
U.S. Class and subclass: 257/686,685,777,778,784-787,734,737,738,723,730,773	9/9/02 2/22/03
Other Documentation: foreign patents and literature in 257//686,685,777,778,784-787,734,737,738,723,730,773	9/9/02 2/22/03
Electronic data base(s): U.S. Patents EAST	9/9/02 2/22/03

Papers related to this application may be submitted to Technology Center 2800 by facsimile transmission. Papers should be faxed to Technology Center 2800 via the Technology Center 2800 Fax center located in Crystal Plaza 4-5B15. The faxing of such papers must conform with the notice published in the Official Gazette, 1096 OG 30 (November 15, 1989). The Technology Center 2800 Fax Center number is (703) 308-7722 or 24. Only Papers related to Technology Center 2800 APPLICATIONS SHOULD BE FAXED to the GROUP 2800 FAX CENTER.

Any inquiry concerning this communication or any earlier communication from the examiner should be directed to *Examiner Alexander Williams* whose telephone number is **(703) 308-4863**.

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Any inquiry of a general nature or relating to the status of this application should be directed to the *Technology Center 2800* receptionist whose telephone number is (703) 308-0956.

2/22/03

Primary Examiner
Alexander O. Williams